

ABSTRACT OF THE DISCLOSURE

In a liquid phase growth process comprising
immersing a substrate in a melt held in a crucible, a
crystal material having been dissolved in the melt, and
5 growing a crystal on the substrate, at least a group of
substrates to be immersed in the melt held in the
crucible are fitted to the supporting rack at a
position set aside from the center of rotation of the
crucible or supporting rack, and the crystal is grown
10 on the surface of the substrate thus disposed. This
can provide a liquid phase growth process which can
attain a high growth rate, can enjoy uniform
distribution of growth rate in each substrate and
between the substrates even when substrates are set in
15 a large number in one batch, and can readily keep the
melt from reaction and contamination even when the
system has a large size, and provide a liquid phase
growth system suited for carrying out the process.

TECHNICAL FIELD